

Daniel C Worledge

List of Publications by Year in descending order

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43
papers

2,871
citations

218677

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45
times ranked

3034
citing authors

#	ARTICLE	IF	CITATIONS
1	Spin-Transfer-Torque MRAM: the Next Revolution in Memory. , 2022, , .		8
2	Reliable Five-Nanosecond Writing of Spin-Transfer Torque Magnetic Random-Access Memory. IEEE Magnetics Letters, 2019, 10, 1-4.	1.1	14
3	Materials for spin-transfer-torque magnetoresistive random-access memory. MRS Bulletin, 2018, 43, 352-357.	3.5	49
4	Theory of Spin Torque Switching Current for the Double Magnetic Tunnel Junction. IEEE Magnetics Letters, 2017, 8, 1-5.	1.1	34
5	Dependence of Voltage and Size on Write Error Rates in Spin-Transfer Torque Magnetic Random-Access Memory. IEEE Magnetics Letters, 2016, 7, 1-4.	1.1	119
6	A new spin on magnetic memories. Nature Nanotechnology, 2015, 10, 187-191.	31.5	645
7	Materials investigation for thermally-assisted magnetic random access memory robust against 400°C temperatures. Journal of Applied Physics, 2015, 117, .	2.5	9
8	Perpendicular Magnetic Anisotropy and Easy Cone State in Ta/Co ₆₀ /Fe ₂₀ /B ₂₀ /MgO. IEEE Magnetics Letters, 2015, 6, 1-4.	1.1	55
9	Development of perpendicularly magnetized Ta CoFeB MgO-based tunnel junctions at IBM (invited). Journal of Applied Physics, 2014, 115, .	2.5	37
10	Electric field-induced ferromagnetic resonance in a CoFeB/MgO magnetic tunnel junction under dc bias voltages. Applied Physics Letters, 2014, 105, .	3.3	44
11	Demonstration of bi-directional microwave-assisted magnetic reversal in synthetic ferrimagnets. Applied Physics Letters, 2013, 103, .	3.3	4
12	Impact of Ta Diffusion on the Perpendicular Magnetic Anisotropy of Ta/CoFeB/MgO. IEEE Magnetics Letters, 2013, 4, 1000104-1000104.	1.1	90
13	Optimization of Tunneling Magnetoresistance in Perpendicular Magnetic Tunnel Junctions With Co Pd Reference Layers. IEEE Magnetics Letters, 2013, 4, 3000104-3000104.	1.1	23
14	(Invited) Recent Developments in ST-MRAM, Including Scaling. ECS Transactions, 2013, 58, 117-125.	0.5	4
15	Spin torque switching of 20-nm magnetic tunnel junctions with perpendicular anisotropy. Applied Physics Letters, 2012, 100, .	3.3	256
16	Demonstration of ultralow bit error rates for spin-torque magnetic random-access memory with perpendicular magnetic anisotropy. IEEE Magnetics Letters, 2011, 2, 3000204-3000204.	1.1	82
17	A Study of Write Margin of Spin Torque Transfer Magnetic Random Access Memory Technology. IEEE Transactions on Magnetics, 2010, 46, 2322-2327.	2.1	115
18	Resonant Switching of Two Dipole-Coupled Nanomagnets. IEEE Transactions on Magnetics, 2010, 46, 2112-2115.	2.1	5

#	ARTICLE	IF	CITATIONS
19	Micromagnetics of Spin-Flop Bilayers: S, C, and Vortex Spin States. IEEE Transactions on Magnetics, 2010, 46, 2124-2127.	2.1	8
20	Investigations of half and full select disturb rates in a toggle magnetic random access memory. Applied Physics Letters, 2008, 92, 192510.	3.3	3
21	Theory for toggle magnetic random access memory: The asymmetric case. Applied Physics Letters, 2007, 91, 162509.	3.3	5
22	Theory for symmetric toggle magnetic random access memory. Applied Physics Letters, 2007, 90, 222506.	3.3	14
23	Two-level BEOL processing for rapid iteration in MRAM development. IBM Journal of Research and Development, 2006, 50, 41-54.	3.1	31
24	Rapid-turnaround characterization methods for MRAM development. IBM Journal of Research and Development, 2006, 50, 55-67.	3.1	22
25	Single-domain model for toggle MRAM. IBM Journal of Research and Development, 2006, 50, 69-79.	3.1	30
26	Low power scaling using parallel coupling for toggle magnetic random access memory. Applied Physics Letters, 2006, 88, 262505.	3.3	10
27	Thermally activated switching in spin-flop tunnel junctions. Applied Physics Letters, 2005, 86, 252506.	3.3	28
28	Reduction of positional errors in a four-point probe resistance measurement. Applied Physics Letters, 2004, 84, 1695-1697.	3.3	19
29	Magnetic phase diagram of two identical coupled nanomagnets. Applied Physics Letters, 2004, 84, 2847-2849.	3.3	80
30	Spin flop switching for magnetic random access memory. Applied Physics Letters, 2004, 84, 4559-4561.	3.3	114
31	Magnetoresistance measurement of unpatterned magnetic tunnel junction wafers by current-in-plane tunneling. Applied Physics Letters, 2003, 83, 84-86.	3.3	206
32	Conducting atomic-force-microscope electrical characterization of submicron magnetic tunnel junctions. Applied Physics Letters, 2003, 82, 4522-4524.	3.3	34
33	Negative Spin-Polarization of SrRuO ₃ . Physical Review Letters, 2000, 85, 5182-5185.	7.8	113
34	Magnetoresistive double spin filter tunnel junction. Journal of Applied Physics, 2000, 88, 5277-5279.	2.5	94
35	Effect of annealing temperature on local distortion of La _{0.67} Ca _{0.33} MnO ₃ thin films. Physical Review B, 2000, 61, 11373-11378.	3.2	26
36	Maki analysis of spin-polarized tunneling in an oxide ferromagnet. Physical Review B, 2000, 62, 447-451.	3.2	47

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37	Spin-polarized tunneling in $\text{La}_{0.67}\text{Sr}_{0.33}\text{MnO}_3$. <i>Applied Physics Letters</i> , 2000, 76, 900-902.	3.3	65
38	The effect of the annealing temperature on the local distortion of $\text{La}_{0.67}\text{Ca}_{0.33}\text{MnO}_3$ thin films. <i>Journal of Synchrotron Radiation</i> , 1999, 6, 682-684.	2.4	0
39	Transport across conducting ferromagnetic oxide/metal interfaces. <i>Applied Physics Letters</i> , 1998, 73, 1736-1738.	3.3	36
40	On-site Coulomb repulsion in the small polaron system $\text{La}_{1-x}\text{Ca}_x\text{MnO}_3$. <i>Physical Review B</i> , 1998, 57, 15267-15271.	3.2	88
41	Growth and small polaron properties of epitaxial $\text{La}_{1-x}\text{Ca}_x\text{MnO}_3$ thin films. <i>Journal of Applied Physics</i> , 1998, 83, 5913-5916.	2.5	20
42	Dynamo waves in semi-infinite and finite domains. <i>Proceedings of the Royal Society A: Mathematical, Physical and Engineering Sciences</i> , 1997, 453, 119-143.	2.1	21
43	Anneal-tunable Curie temperature and transport of $\text{La}_{0.67}\text{Ca}_{0.33}\text{MnO}_3$. <i>Journal of Applied Physics</i> , 1996, 80, 5158-5161.	2.5	160